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APPLICATION NO. FILING DATE		· FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.		
09/764,242	09/764,242 01/19/2001		George Wong	CS98-070B	8930	
28112	7590	04/24/2003				
GEORGE C	SAILE	& ASSOCIATE	EXAMINER			
	8 DAVIS AVENUE OUGHKEEPSIE, NY 12603 DIAZ, JOSE R					
				ART UNIT	PAPER NUMBER	
		•		2815		
				DATE MAILED: 04/24/2003		

Please find below and/or attached an Office communication concerning this application or proceeding.

		Applica	tion No.	pplicant(s)	(M~
		09/764,	242	WONG, GEORGE	
	Office Action Summary	Examin		Art Unit	
		José R [2815	
Donie d &	The MAILING DATE of this communica			t with the correspondence add	ress
r enound	л керіу				
- External frame - If the - If NO - Failur - Any r	ORTENED STATUTORY PERIOD FOR MAILING DATE OF THIS COMMUNICA nasions of time may be available under the provisions of 3 SIX (6) MONTHS from the mailing date of this communic period for reply specified above is less than thirty (30) day period for reply is specified above, the maximum statuto re to reply within the set or extended period for reply will, eply received by the Office later than three months after the patent term adjustment. See 37 CFR 1.704(b).	ATION. FOR 1.136(a). In no ecation. ays, a reply within the strong period will apply and by statute. Cause the action.	vent, however, ma atutory minimum of will expire SIX (6) N	y a reply be timely filed thirty (30) days will be considered timely. MONTHS from the mailing date of this com	munication.
1)[Responsive to communication(s) filed	on <u>08 April</u> 2003			
2a) <u></u> □		☐ This action is			
3)	Since this application is in condition for			natters prosecution as to the	morite ie
Dispositi	closed in accordance with the practice on of Claims	under <i>Ex parte</i> (Quayle, 1935	C.D. 11, 453 O.G. 213.	ments is
4) 🖂	Claim(s) 18-22 is/are pending in the ap	plication.	•		
4	4a) Of the above claim(s) is/are w	withdrawn from co	nsideration.		
5)	Claim(s) is/are allowed.				
6)⊠	Claim(s) <u>18-22</u> is/are rejected.				
7)	Claim(s) is/are objected to.				
8)[Claim(s) are subject to restriction	n and/or election i	equirement.		
Application	on Papers		•		
9)∐ Т	he specification is objected to by the Ex	kaminer.			
10)∐ T	he drawing(s) filed on is/are: a)[accepted or b)	objected to by	the Examiner.	
	Applicant may not request that any objection	on to the drawing(s	be held in abo	eyance. See 37 CFR 1.85(a).	
11) 🗌 T	he proposed drawing correction filed on	ı is: a)∏ a	pproved b)	disapproved by the Examiner.	
	If approved, corrected drawings are require	· -	ffice action.		•
12) 🔲 T	he oath or declaration is objected to by	the Examiner.			
Priority u	nder 35 U.S.C. §§ 119 and 120				
13) 🔲 🗸	Acknowledgment is made of a claim for	foreign priority ur	der 35 U.S.C	. § 119(a)-(d) or (f).	
a)[All b) Some * c) None of:				
	1. Certified copies of the priority docu	uments have bee	n received.		
2	2. Certified copies of the priority docu	uments have bee	n received in	Application No	
	B. Copies of the certified copies of th application from the Internation ee the attached detailed Office action for	ne priority documenal Bureau (PCT	ents have bee Rule 17.2(a))	n received in this National Sta	age
	knowledgment is made of a claim for do				unlication)
	☐ The translation of the foreign langua				piication).
15)⊠ Á	cknowledgment is made of a claim for do	omestic priority u	nder 35 U.S.(C. §§ 120 and/or 121.	
ttachment(:		-			
) 🔲 Notice	of References Cited (PTO-892) of Draftsperson's Patent Drawing Review (PTO-9- ation Disclosure Statement(s) (PTO-1449) Paper N		4) Interview 5) Notice of 6) Other:	v Summary (PTO-413) Paper No(s). f Informal Patent Application (PTO-15	
Patent and Trac O-326 (Rev.	A . A	ffice Action Summa	·v	Part of Pan	or No. 44

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DETAILED ACTION

Continued Examination Under 37 CFR 1.114

➤ A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on April 8, 2003 has been entered.

Claim Rejections - 35 USC § 102

> The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.
- Claims 18 and 19 are still rejected under 35 U.S.C. 102(e) as being anticipated by Saitou et al. (US Pat. No. 5,739,546). See Office action mailed on June 13, 2002.

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Claim Rejections - 35 USC § 103

> The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

- (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- ➤ Claim 20 is still rejected under 35 U.S.C. 103(a) as being unpatentable over Saitou et al. (US Pat. No. 5,739,546) in view of Lou (US Pat. No. 5,759,906). See Office action mailed on June 13, 2002.
- > Claims 21-22 are still rejected under 35 U.S.C. 103(a) as being unpatentable over Saitou et al. (US Pat. No. 5,739,546). See last Office action mailed on June 13, 2002.

Response to Arguments

Applicant's arguments filed April 8, 2003 have been fully considered but they are not persuasive. In summary, Applicant argues that Saitou et al. fails to teach a patterned fill layer, a planar silicon oxide layer, and a multilevel metal structure. However, the Examiner disagrees. With regards to the patterned fill layer, the reference Saitou et al. teaches a patterned conductive layer formed in the semiconductor region (2) and in the kerf areas (3) (see Figure 2). Please note, that the patterned conductive layer formed in the semiconductor region is identified by the reference sign (10), and the patterned conductive layer formed in the kerf areas is identified by the reference sign (6)

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(see Figure 1), both formed of the <u>same</u> metal material (please note that regions 6 and 10 are shown in Figure 2 having the same line pattern). In addition, the reference Saitou et al. teaches that the kerf area (3) are <u>filled</u> with the conductive layer (8) (see Figure 1) and the patterned conductive layer (6) (see Figure 2). Please note that Figure 1 does not show the patterned conductive layer (6) because the patterned conductive layer (6) is formed under the conductive layer (8) (see Figure 2). Thus, the patterned conductive layer (6) of Saitou et al. is a "patterned fill layer" since the patterned conductive layer (6) is formed in the kerf areas and is formed of the same metal material as the patterned conductive layer formed in the semiconductor region.

With regards to the planar silicon oxide layer, the Examiner disagrees with Applicant. Saitou et al. teaches a silicon oxide layer (7) formed on the patterned fill layer (6) (see Figure 2). After a carefully review of the drawings, the Examiner concluded that Figure 3, which is a cross sectional view of Figure 1, further provides the teaching of a planar layer, as required by Applicant. Figure 3 shows that, the silicon oxide layer (7) is planar over the surface of the patterned fill layer (6). Consequently, the reference Saitou et al. anticipates the claimed limitation since Saitou et al. teach a planar silicon oxide layer formed over the patterned fill layer.

Finally, with regards to the multilevel metal structure, the Examiner would like to point out that the reference Saitou et al. clearly anticipates such a limitation in column 6, lines 61-65, wherein Saitou et al. states that multilevel metal structure can also be formed as required. Therefore, Saitou et al. anticipates the claimed limitation of providing a multilevel metal structure.

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Correspondenc

Any inquiry concerning this communication or earlier communications from the

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examiner should be directed to José R Díaz whose telephone number is (703) 308-

6078. The examiner can normally be reached on 9:00-5:00 Monday, Tuesday,

Thursday and Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, Eddie Lee can be reached on (703) 308-1690. The fax phone numbers for

the organization where this application or proceeding is assigned are (703) 308-7722 for

regular communications and (703) 746-3891 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or

proceeding should be directed to the receptionist whose telephone number is (703) 308-

0956.

JRD

April 22, 2003

EDDIE LEE

SUPERVISORY PATENT EXAMINER

TECHNOLOGY CENTER 2800